

<b>Supplemental</b> <b>INFORMATION DISCLOSURE CITATION</b> (Use several sheets if necessary)	ATTY DOCKET NO. <b>CS.174</b> SERIAL NO. <b>10/039,284</b> Richard A. Blanchard et al. FILING <b>12/31/01</b> GROUP <b>2811</b>
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**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
PC	1.	10/039,241		Blanchard			12/31/2001
PC	2.	10/038,845		Blanchard			12/31/2001
PC	3.	09/970,758		Blanchard et al.			10/4/2001
PC	4.	2001/0053568A1	12/20/2001	Deboy et al.	438	138	
PC	5.	2001/0036704A1	11/1/2001	Huetting et al.	438	270	
PC	6.	2001/0026977A1	10/4/2001	Hattori et al.	438	268	
PC	7.	5,216,275	6/1/93	Cheo	257	493	
PC	8.	5,108,783	4/28/92	Tanigawa et al.	437	63	
PC	9.	4,893,160	1/9/90	Blanchard	357	23.4	
PC	10.	4,711,017	12/8/87	Lammert	437	20	

**FOREIGN PATENT DOCUMENTS**

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

PC	1.	Xing Bi Chen et al., "A Novel High-Voltage Sustaining Structure with Buried Oppositely Doped Regions," <i>IEEE Transactions on Electron Devices</i> , Vol. 47, No. 6, June 2000, pp. 1280-1285.
PC	2.	N. Cezac et al., "A New Generation of Power Unipolar Devices: the Concept of the Floating Islands MOS Transistor (FLIMOST)," <i>Proceedings of the 12th International Symposium on Power Semiconductor Devices &amp; ICs, Toulouse, France, May 22-25, 2000</i> , pp. 69-72.

EXAMINER  
**PHAT X. CAO**

DATE CONSIDERED **3/11/04**

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



Docket No.: 74

Substitute for form 1449A/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		<i>Complete If Known</i>			
		Application Number	10/039,284		
		Filing Date	12/31/01		
		First Named Inventor	Richard A. Blanchard et al.		
		Group Art Unit	2814		
		Examiner Name	Phat X. Cao		
Sheet	1	of	1	Attorney Docket Number	GS 174

Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM- DD-YYYY
		Number	Class/Subclass		
PC	1.	5,912,497	257/366	Bantval Jayant Baliga	06/15/1999

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM- DD-YYYY	T
		Office <sup>2</sup>	Number <sup>3</sup>	Class/Subclass			

Examiner Signature	PHAT X. CAO	Date Considered	3/11/04
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<sup>1</sup> Unique citation designation number. <sup>2</sup> See Kinds of U.S. Patent Documents. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English Language Translation is attached.